

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-12 (cancelled)

Claim 13. (currently amended) A non volatile memory, comprising:

- a) flash memory cells organized in rows and columns,
- b) cells in a row are interconnected by a word line connecting to control gates of said flash memory cells in said row,
- c) cell layout in a first column of cells mirrors having a same said cell layout in adjacent second and a third columns of cells, whereby a bit line connects to a select and control portion of a channel of a memory device of said cells in the first column and the bit line connects to a stacked gate portion of said channel of the third column of cells, producing a first pair of adjacent columns with drains close together and a second pair of adjacent columns with sources close together,
- d) asaid bit line extends full length of said columns, laying between said cells of said first pair of adjacent and third columns, and connecting said drains of said first pair of adjacent columns to a sense amplifier,
- e) a source line extends full length of said columns, laying between said cells of said first and second columns, whereby said source line connects to a stacked gate

portion of said channel of the first column of cells and the source line connects to a select and control portion of said channel of the second column of cells, second pair of adjacent columns and connecting said sources of said second pair of adjacent columns to source voltages.

f) a program operation of said flash memory cells organized by a vertical page comprising said memory cells in the first column associated with said source line, whereby a source line voltage and a bit line voltage of said vertical page are set for said program operation and a word line program voltage is stepped from cell to cell in said first column,

g) an erase operation of said flash memory cells organized by a horizontal block comprising a first row of cells adjacent to a second row of cells and whereby all bit lines, source lines and word lines of said horizontal block are coupled to a same low voltage and then word lines coupled to cells in said horizontal block to be erased are biased to an erase voltage.

h) said cell layout in asaid columns is a same said cell layout in adjacent columns producing a first adjacent column with drains of cells connected to a first source line and sources of cells connected to a first bit line, and a second adjacent column with sources of cells connected to said first source line and drains of cells in said second adjacent column connected to a second bit line, allowing vertical page programming and horizontal page/block erase.

14. (currently amended) The non volatile memory of claim 13 wherein, said bit
~~lines extend full length of said columns, laying between a first pair of adjacent columns,~~
~~connecting to said drains of a first column of said first pair of adjacent columns, to said~~
~~sources of a second column of said first pair of adjacent columns, and provide a path to~~
~~read data stored in said cells connecting to a sense amplifier when performing a read~~
operation.

15. (currently amended) The non volatile memory of claim 13 wherein, said
~~source lines extend full length of said columns, laying between a second pair of~~
~~adjacent columns, connecting to said sources of said cells of the first column of said~~
~~second pair of adjacent columns, connecting to said drains of said cells of the second~~
~~column second pair of adjacent columns, and connecting to source voltages.~~

Claims 16-25 (canceled)